KF6N70I

N CHANNEL MOS FIELD EFFECT TRANSISTOR

General Description

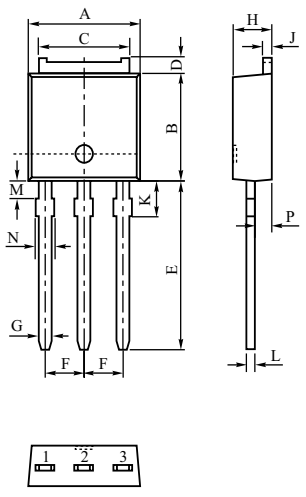
This planar stripe MOSFET has better characteristics, such as fast switching time, fast reverse recovery time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for electronic ballast and switching mode power supplies.

FEATURES

· V_{DSS}= 700V, I_D= 6A

· Drain-Source ON Resistance : $R_{DS(ON)}$=1.65Ω(Max) @V_{GS} = 10V

· Qg(typ) = 19nC



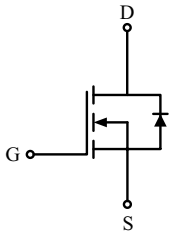
DIM	MILLIMETERS
A	6.6±0.2
B	6.1±0.2
C	5.34±0.3
D	0.7±0.2
E	9.3±0.3
F	2.3±0.2
G	0.76±0.1
H	2.3±0.1
J	0.5±0.1
K	1.8±0.2
L	0.5±0.1
M	1.0±0.1
N	0.96 MAX
P	1.02±0.3

IPAK(1)

MAXIMUM RATING (Tc=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	@T_C=25℃	I_D	5.2	A
	@T_C=100℃		3.3	
	Pulsed (Note1)	I_{DP}	15	
Single Pulsed Avalanche Energy (Note 2)		E_{AS}	160	mJ
Repetitive Avalanche Energy (Note 1)		E_{AR}	4.2	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Drain Power Dissipation	Tc=25℃	P_D	119	W
	Derate above 25℃		0.95	W/℃
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 150	℃
Thermal Characteristics				
Thermal Resistance, Junction-to-Case		R_{thJC}	1.05	℃/W
Thermal Resistance, Junction-to-Ambient		R_{thJA}	110	℃/W

PIN CONNECTION



ELECTRICAL CHARACTERISTICS (Tc=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	700	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_j$	I_D=250μA, Referenced to 25°C	-	0.65	-	V/°C
Drain Cut-off Current	I_{DSS}	V_{DS}=700V, V_{GS}=0V,	-	-	10	μA
Gate Threshold Voltage	V_{th}	V_{DS}=V_{GS}, I_D=250μA	2.5	-	4.5	V
Gate Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	-	-	±100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3A	-	1.42	1.65	Ω
Dynamic						
Total Gate Charge	Q_g	V_{DS}=560V, I_D=6A V_{GS}=10V (Note4,5)	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	4	-	
Gate-Drain Charge	Q_{gd}		-	8	-	
Turn-on Delay time	$t_{d(on)}$	V_{DD}=350V I_D=6A R_G=25Ω (Note4,5)	-	34	-	ns
Turn-on Rise time	t_r		-	32	-	
Turn-off Delay time	$t_{d(off)}$		-	90	-	
Turn-off Fall time	t_f		-	33	-	
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	785	-	pF
Output Capacitance	C_{oss}		-	91	-	
Reverse Transfer Capacitance	C_{rss}		-	9.1	-	
Source-Drain Diode Ratings						
Continuous Source Current	I_S	V_{GS}<V_{th}	-	-	6	A
Pulsed Source Current	I_{SP}		-	-	24	
Diode Forward Voltage	V_{SD}	I_S=6.0A, V_{GS}=0V	-	-	1.4	V
Reverse Recovery Time	t_{rr}	I_S=6.0A, V_{GS}=0V, dIs/dt=100A/μs	-	345	-	ns
Reverse Recovery Charge	Q_{rr}		-	3	-	μC

Note 1) Repetivity rating : Pulse width limited by junction temperature.

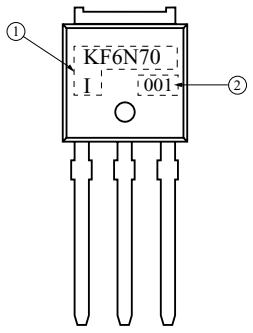
Note 2) L=8.4mH, I_S=6.0A, V_{DD}=50V, R_G=25Ω, Starting T_j=25°C.

Note 3) I_S≤6A, dI/dt≤100A/μs, V_{DD}≤BV_{DSS}, Starting T_j=25°C.

Note 4) Pulse Test : Pulse width ≤300μs, Duty Cycle≤2%.

Note 5) Essentially independent of operating temperature.

Marking



① PRODUCT NAME

② LOT NO

Fig 1. I_D - V_{DS}

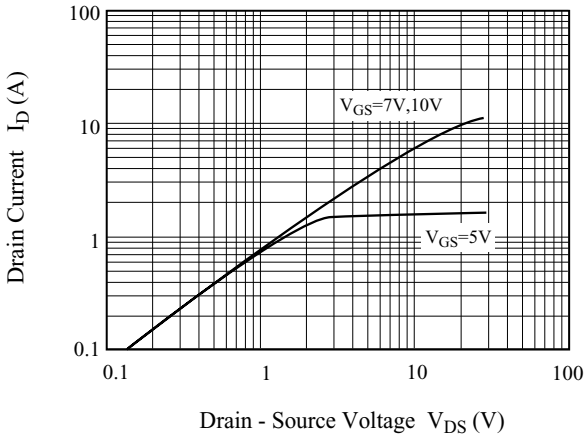


Fig 2. I_D - V_{GS}

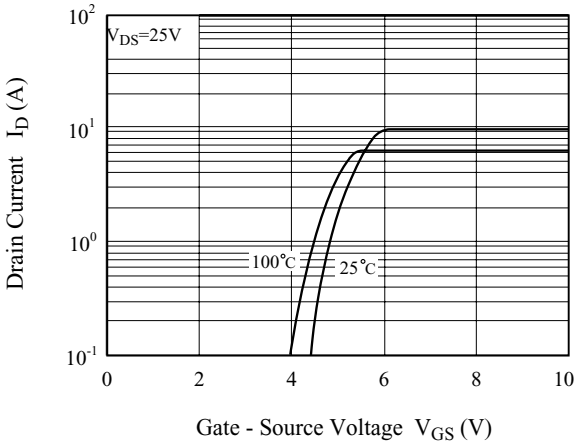


Fig 3. BV_{DSS} - T_j

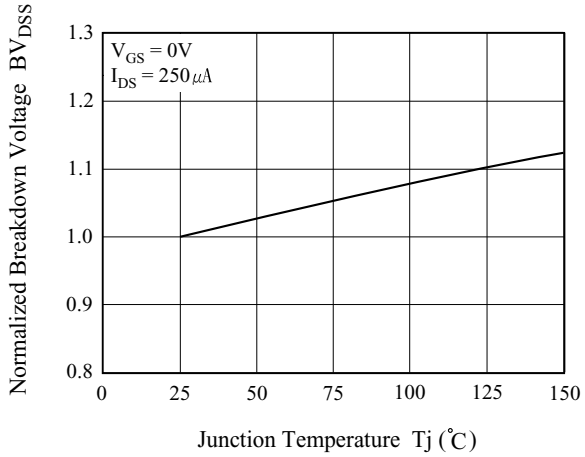


Fig 4. $R_{DS(ON)}$ - I_D

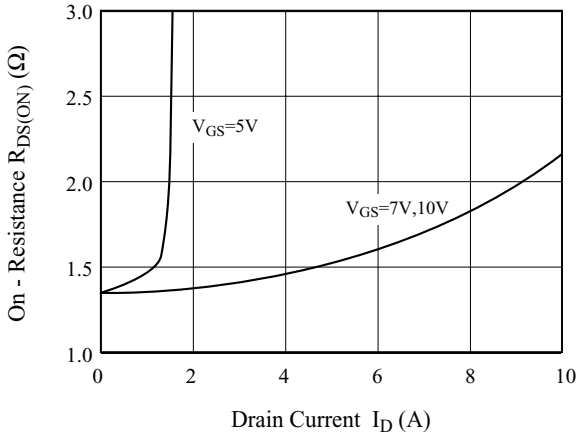


Fig 5. I_S - V_{SD}

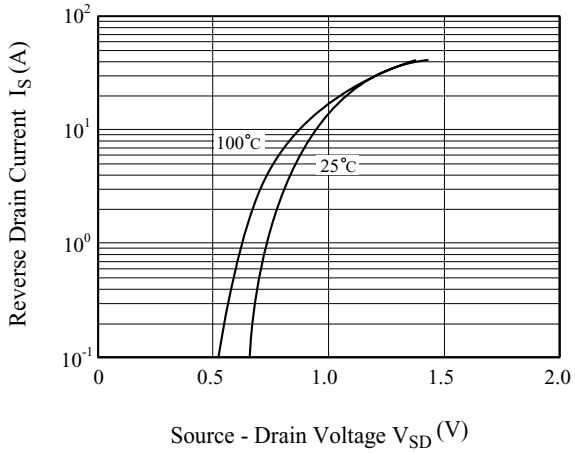


Fig 6. $R_{DS(ON)}$ - T_j

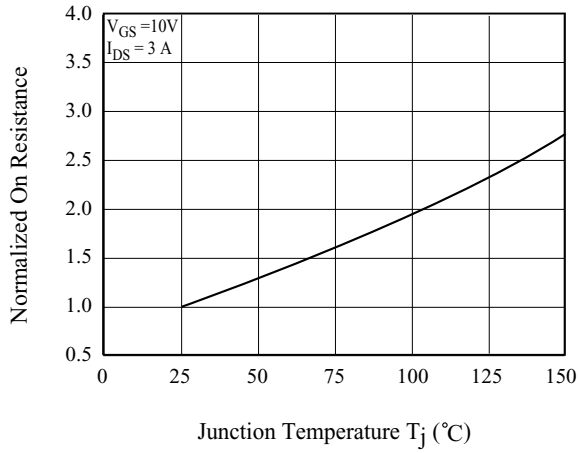


Fig 7. C - V_{DS}

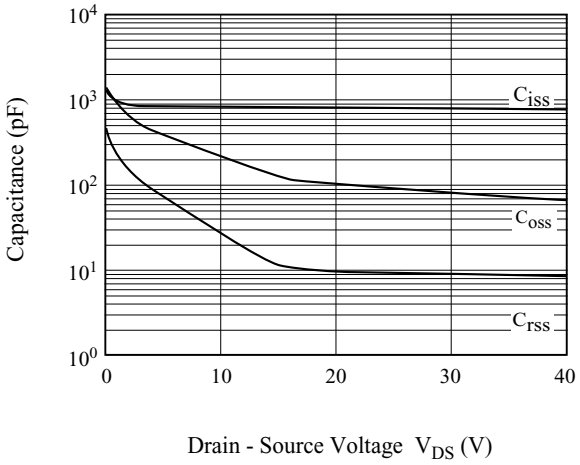


Fig 8. Q_g- V_{GS}

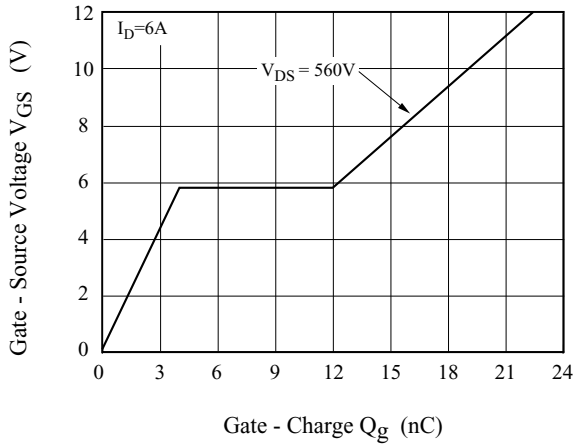


Fig 9. Safe Operation Area

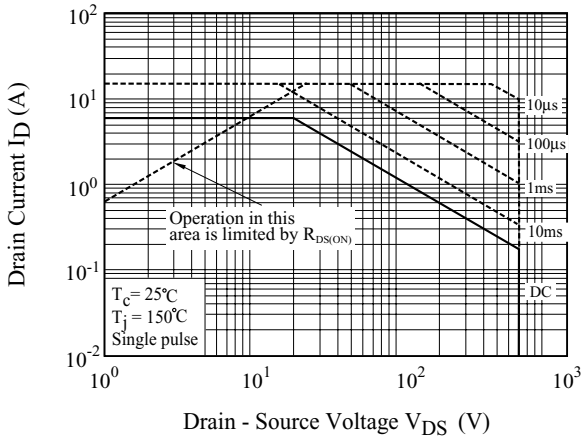


Fig 10. Transient Thermal Response Curve

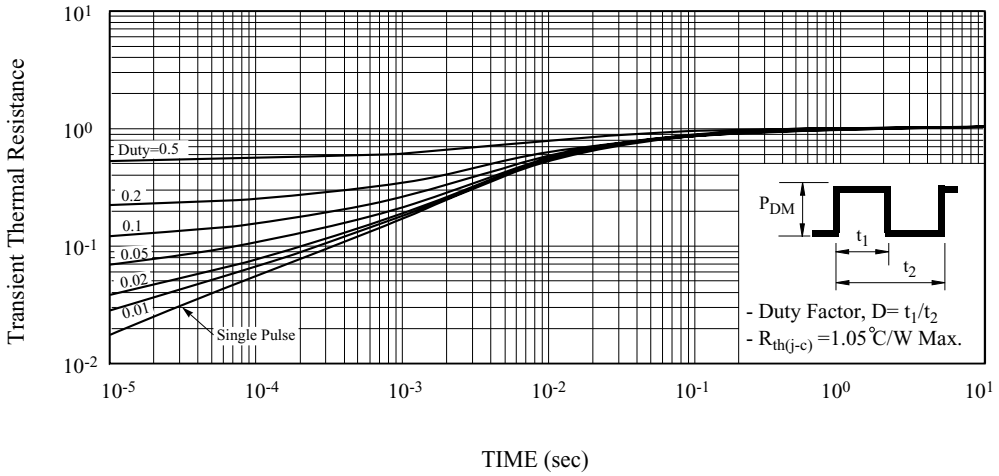
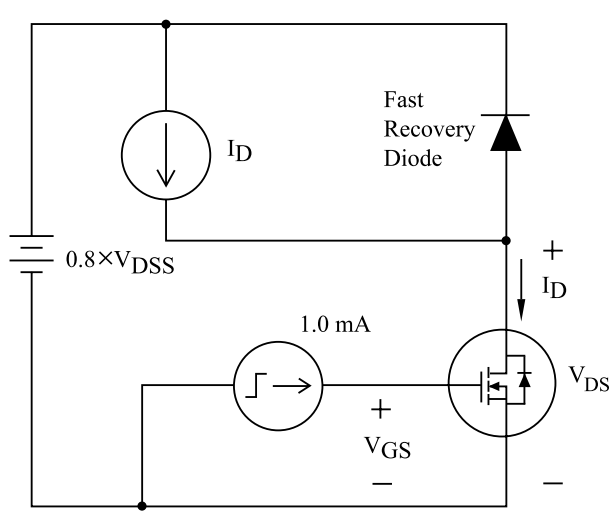


Fig 11. Gate Charge



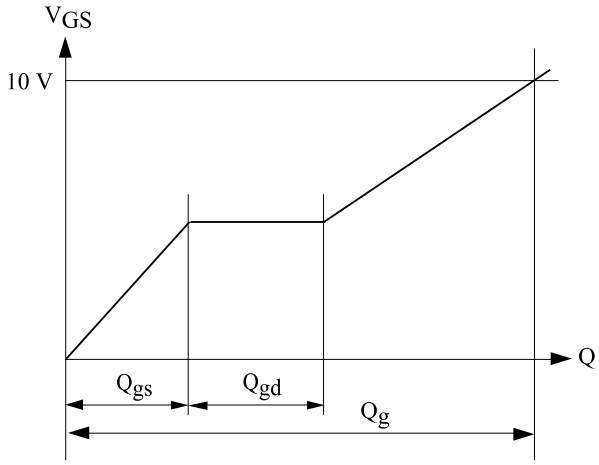
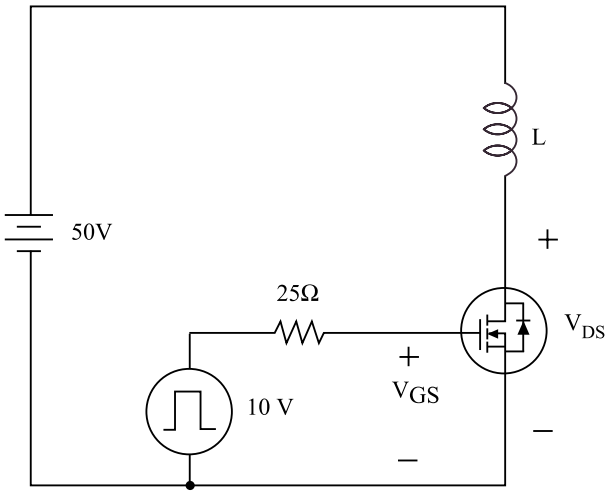


Fig 12. Single Pulsed Avalanche Energy



$$E_{AS}=\frac{1}{2}LI_{AS}^2\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

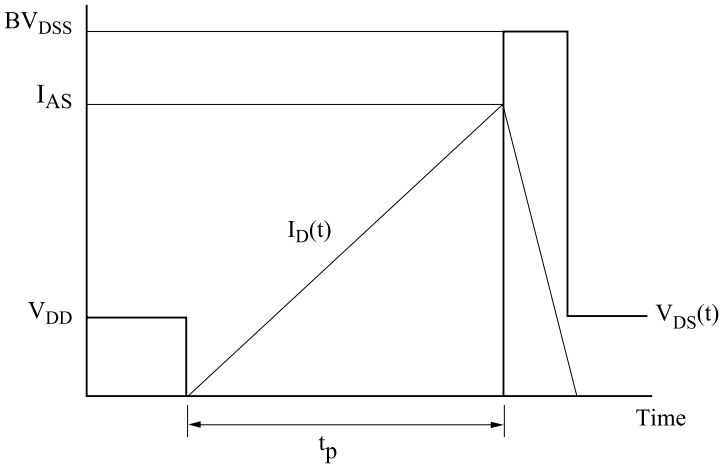
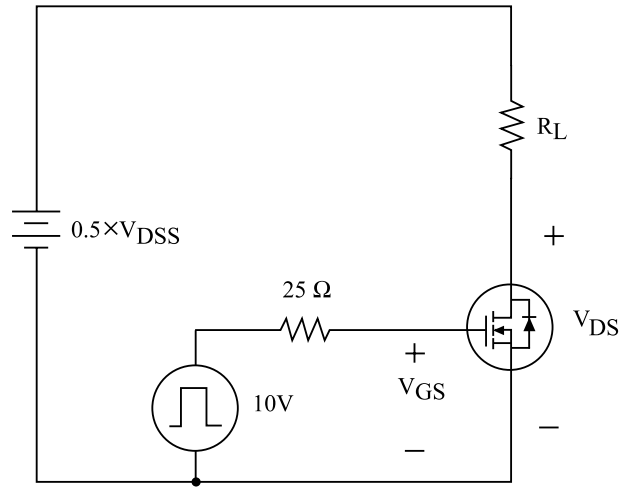


Fig 13. Resistive Load Switching



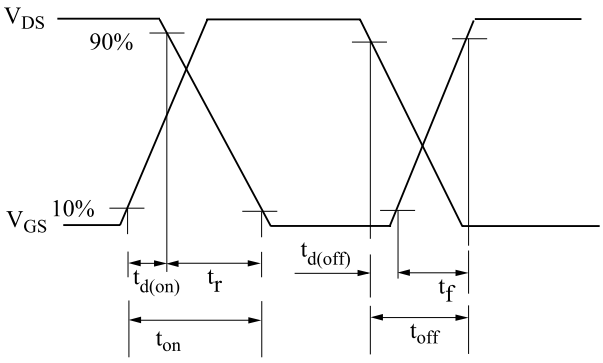


Fig 14. Source - Drain Diode Reverse Recovery and dv /dt